

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

ATTORNEY DOCKET NUMBER: 10005237-3

IN RE APPLICATION OF: U.S. Patent No. 7,103,972

USPTO CONFIRMATION CODE: 5327

APPLICATION NO.: 10/695,147

FILED: Oct. 28, 2003

EXAMINER: A. Dexter Tugbang

GROUP ART UNIT: 3729

FOR: METHOD OF FABRICATING A FLUID EJECTION DEVICE

37 CFR 1.322 & 37 CFR 1.323 REQUEST FOR CERTIFICATE OF CORRECTION

HONORABLE COMMISSIONER OF PATENTS & TRADEMARKS

Sir:

The following is a request for a certificate of correction in Serial Number 10/695,147, now Patent Number 7,103,972.

A certificate of correction under 35 USC 254 is respectfully requested in the above-identified patent.

☒ All errors were the fault of the USPTO, no fee required. In the event that a further fee is required, please charge the amount to Deposit Account No. 082025.

☐ All errors were the fault of the applicant and, accordingly, please charge **\$100.00** to our Deposit Account No. 082025. In the event that a further fee is required, please charge the amount to the same Deposit Account.

☐ The errors were the fault of both the applicant and USPTO and, accordingly, please charge **\$100.00** to our Deposit Account No. 082025. In the event that a further fee is required, please charge the amount to the same Deposit Account.

The exact locations where the errors appear in the patent and patent application are as follows:

On the face page, in field (75), in "Inventors", in column 1, line 1, delete "C rvallis" and insert - - Corvallis - -, therefor.
(Oath or Declaration filed on Oct. 28, 2003, page 1 of 2, first inventor's residence, line 1)

On the face page, in field (57), under "Abstract", in column 2, lines 1-3, delete "A fluid ejection device comprising a composite substrate, wherein the composite substrate has two substrates with a patterned etch mask therebetween, and a fluid channel." and insert - - A Method of fabricating a fluid ejection device comprising: bonding a top surface of a first substrate to a bottom surface of a second substrate, wherein a patterned etch mask layer is formed on at least one of the top surface of the first substrate and the bottom surface of the second substrate; and etching a fluid channel in the first and second substrates extending through an opening in the patterned etch mask layer. - -, therefor.
(Amendment to abstract filed on Feb. 03, 2006, page 3, lines 1-5)

In column 2, line 53, delete "second" and insert - - first - -, therefor.
(Preliminary Amendment to specification filed on Oct. 28, 2003, page 2, line 18)

In column 2, line 54, delete "forming" and insert - - form - -, therefor.
(Preliminary Amendment to specification filed on Oct. 28, 2003, page 2, line 19)

In column 6, line 36, in Claim 9, before "surface" delete "to" and insert - - top - -, therefor.
(Amendment to claims filed on May 04, 2006, page 3, in Claim 18, line 4)

The requested corrections are attached on Form PTO 1050.

Respectfully Submitted

3/13/2009
DATE

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**UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION**

Page 1 of 1

PATENT NO. : 7,103,972
APPLICATION NO. : 10/695, 147
ISSUE DATE : Sep. 12, 2006
INVENTOR(S) : Chien-Hua Chen, et al.

It is certified that an error appears or errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

On the face page, in field (75), in "Invertors", in column 1, line 1, delete "C rvallis" and insert - - Corvallis - -, therefor.

On the face page, in field (57), under "Abstract", in column 2, lines 1-3, delete "A fluid ejection device comprising a composite substrate, wherein the composite substrate has two substrates with a patterned etch mask therebetween, and a fluid channel." and insert - - A Method of fabricating a fluid ejection device comprising: bonding a top surface of a first substrate to a bottom surface of a second substrate, wherein a patterned etch mask layer is formed on at least one of the top surface of the first substrate and the bottom surface of the second substrate; and etching a fluid channel in the first and second substrates extending through an opening in the patterned etch mask layer. - -, therefor.

In column 2, line 53, delete "second" and insert - - first - -, therefor.

In column 2, line 54, delete "forming" and insert - - form - -, therefor.

In column 6, line 36, in Claim 9, before "surface" delete "to" and insert - - top - -, therefor.

MAILING ADDRESS OF SENDER (Please do not use customer number below):

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This collection of information is required by 37 CFR 1.322, and 1.323, and 1.324. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C 122 and 37 CFR 1.14. This collection is estimated to take 1.0 hour to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Attention Certificate of Corrections Branch, Commissioner for Patent, P.O. Box 1450, Alexandria, VA 22313-1450.

If you need assistance in completing the form, call 1-800-PTO-9199 and select option 2.